

In the drawings:

Please replace Fig. 6B and Fig. 6C in the application with the enclosed replacement sheet containing revised Fig. 6B and 6C.

Revised Fig. 6B is a copy of Fig. 19 of U.S. Pat. No. 4,895,810, with reference numerals changed to match those of prior Fig. 6B.

Revised Fig. 6C is a copy of Fig. 16B of U.S. Pat. No. 5,262,336, with reference numerals changed to match those of prior Fig. 6C.

A cross-sectional view of a semiconductor device. A central channel 220 is formed in a substrate 218. The channel 220 is lined with a material 222. On the top surface of the channel 220, there is a layer 224. On the side walls of the channel 220, there are contacts 226. The contacts 226 are connected to a common line 240. The contacts 226 are also connected to a common line 276. The contacts 226 are also connected to a common line 275. The contacts 226 are also connected to a common line 262a. The contacts 226 are also connected to a common line 263. The contacts 226 are also connected to a common line 224.

[illegible]